



Ain Shams University
Faculty of Education
Physics Department

Study of some physical properties of organic dye thin films and photovoltaic application

Thesis Presented by

Lamiaa Mahmoud Diao El-Deen Mohamed

For the degree Master of Teacher's Preparation in Science
(Solid State Physics)

Supervised by

Dr. Attia Abd El-Motteleb Attia

Assistance Prof. of Solid State physics
Physics Dept., Faculty of Education
Ain Shams University

Dr. Enas Abd EL-Fattah El-shazly

Assistance Prof. of Solid State physics
Physics Dept., Faculty of Education
Ain Shams University

Dr. Amal Mohammed Abd El-barry

Assistance Prof. of Solid State physics
Physics Dept., Faculty of Education
Ain Shams University

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Ain Shams University
Faculty of Education
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Researcher name: Lamiaa Mahmoud Diao El-Deen Mohamed

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Supervisors:

1-Dr. Attia Abd El-Motteleb Attia

2- Dr. Enas Abd EL-Fattah El-shazly

3- Dr. Amal Mohammed Abd El-barry

Approval sheet

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Candidate: Lamiaa Mahmoud Daa El-Deen Mohamed

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Board of Advisors

Approved by:

1-Dr. Attia Abd El-Motteleb Attia

Assistance Prof. of Solid State physics
Physics Dept., Faculty of Education
Ain Shams University

2- Dr. Enas Abd EL-Fattah El-shazly

Assistance Prof. of Solid State physics
Physics Dept., Faculty of Education
Ain Shams University

3- Dr. Amal Mohammed Abd El-barry

Assistance Prof. of Solid State physics
Physics Dept., Faculty of Education
Ain Shams University

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